

NOT RECOMMENDED FOR NEW DESIGN USE DMG6402LVT



DMG6402LDM

N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low R_{DS(ON)}
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 2)

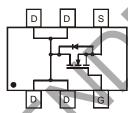
Mechanical Data

- Case: SOT-26
- Case Material Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 2
- Ordering Information: See page 2
- Weight: 0.008 grams (approximate)

SOT-26



TOP VIEW



TOP VIEW Internal Schematic

Maximum Ratings @ $T_A = 25^{\circ}C$ unless otherwise specified

Characterist	ic		Symbol	Value	Unit
Drain-Source Voltage			$V_{\rm DSS}$	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 3)	Steady State	$T_A = 25$ °C $T_A = 70$ °C	l _D	5.3 4.2	А
Pulsed Drain Current (Note 4)			I _{DM}	31	A

Thermal Characteristics

	A 10		
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 3)	P _D	1.12	W
Thermal Resistance, Junction to Ambient T _A = 25°C (Note 3)	$R_{ hetaJA}$	111	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 4. Repetitive Rating, pulse width limited by junction temperature.

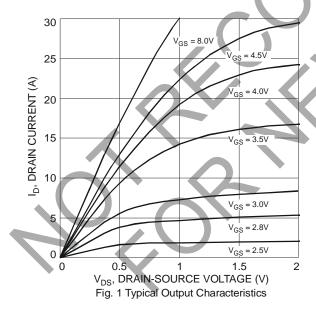


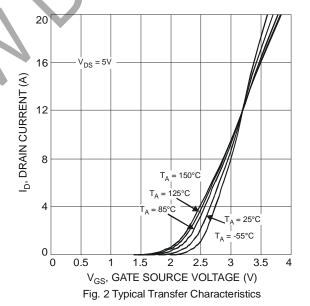
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1.0	μ A	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(th)}	1.0	1.5	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS} (ON)	_	22	27	mΩ	$V_{GS} = 10V, I_D = 7A$	
Static Brain Godice On Resistance	INDS (ON)		32	40	11122	$V_{GS} = 4.5V$, $I_{D} = 5.6A$	
Forward Transfer Admittance	Y _{fs}	-	10	-	S	$V_{DS} = 5V, I_{D} = 7A$	
Diode Forward Voltage	V_{SD}	-	0.75	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C _{iss}	-	404	-	pF	45)()(0)(
Output Capacitance	C _{oss}	-	52		pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	45	- 1	рF	1 = 1:0WHZ	
Gate Resistance	Rg	-	1.51	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_{g}	-	9.2	1	nC		
Gate-Source Charge	Q_{gs}	-	1.2	-	nC /	$V_{GS} = 10V$, $V_{DS} = 15V$, ID =5.8A	
Gate-Drain Charge	Q_{gd}		1.8		nC	*	
Turn-On Delay Time	t _{D(on)}	-	3.41	-	ns		
Turn-On Rise Time	t _r	-	6.18	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(off)}		13.92	-	ns	$R_L = 2.6\Omega$, $R_G = 3\Omega$	
Turn-Off Fall Time	t _f		2.84	A -	ns		

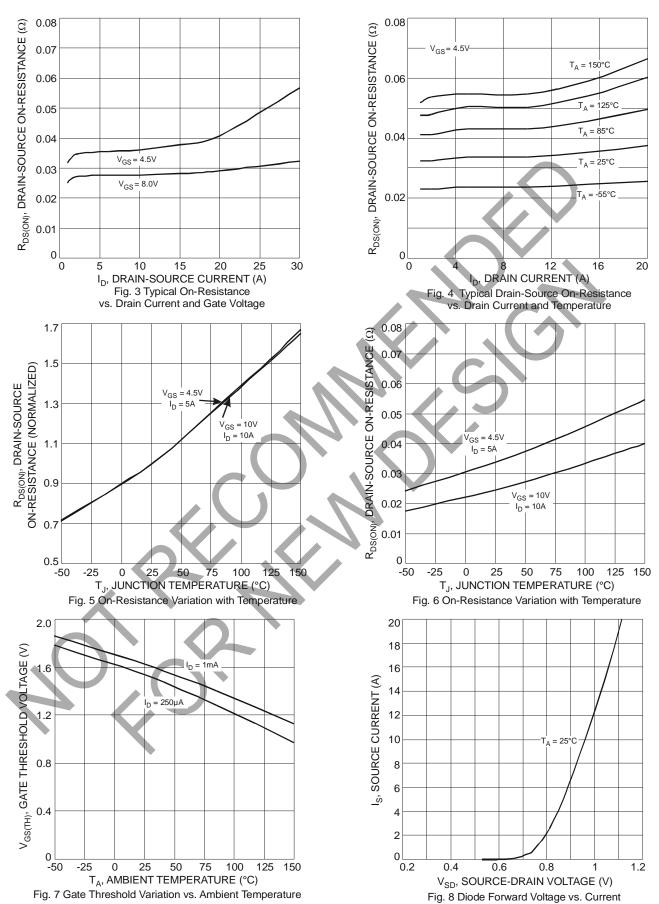
Notes:

- 5. Short duration pulse test used to minimize self-heating effect.
- 6. Guaranteed by design. Not subject to production testing.

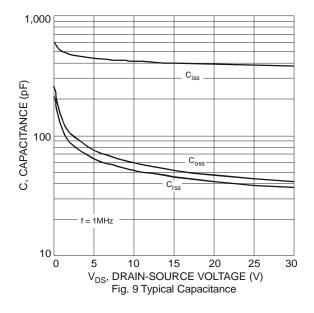


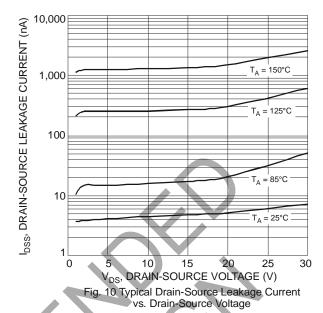












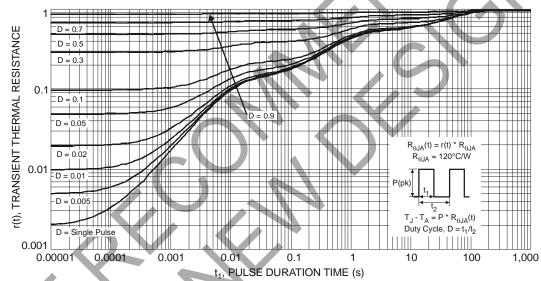


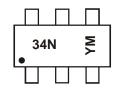
Fig. 11 Transient Thermal Response

Ordering Information (Note 7)

Part Number	Case	Packaging
DMG6402LDM-7	SOT-26	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



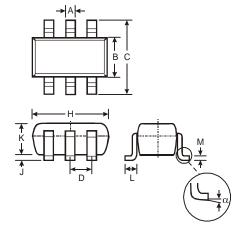
34N= Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	2010		2011	2012	·	2013	2014		2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Au	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

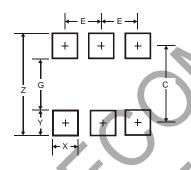


Package Outline Dimensions



	SOT-26						
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
С	2.70	3.00	2.80				
D	_	_	0.95				
Н	2.90	3.10	3.00				
J	0.013	0.10	0.05				
K	1.00	1.30	1.10				
L	0.35	0.55	0.40				
M	0.10	0.20	0.15				
α	0°	8°	-				
All D	All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Υ	0.80
С	2.40
Е	0.95





DMG6402LDM

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